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RFIC Plenary

Chair: Brian Floyd, North Carolina State University, USA

Co-Chair: Osama Shana'a, MediaTek, USA and Donald Y.C. Lie, Texas Tech University, USA






Virtual Event, 10:00-12:00, Monday, 21 June 2021

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Bram Nauta, University of Twente, The Netherlands **A**
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Ahmad Bahai, Texas Instruments, USA **A**

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Chair: Gernot Hueber, Silicon Austria Labs, Austria — Co-Chair: Duane Howard, Amazon Web Services, USA

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¹Stanford University, USA **A** ; ²STMicroelectronics, France **A**
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¹University of Michigan, USA **A** ; ²Caltech, USA **A** ; ³STMicroelectronics, France **A**
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Chair: Kamran Entesari, Texas A&M University, USA

Co-Chair: Domine M.W. Leenaerts, NXP Semiconductors, The Netherlands






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Zhiwei Zong¹, Johan Nguyen¹, Yao Liu², Yang Zhang², Xinyan Tang¹, Giovanni Mangraviti², Piet Wambacq¹
¹Vrije Universiteit Brussel, Belgium **A** ; ²imec, Belgium **A**
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¹Georgia Tech, USA **A** ; ²Samsung, Korea **A**
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Chair: Alvin Joseph, GLOBALFOUNDRIES, USA — Co-Chair: Fred Lee, Twenty/Twenty Therapeutics, USA

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¹Tsinghua University, China **A** ; ²Southeast University, China **A**
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¹POSTECH, Korea **A** ; ²Samsung, Korea **A**
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¹CEA-Leti, France **A** ; ²Keysight Technologies, France **A** ; ³Amkor Technology, Portugal **A**

RTu4F: High-Performance Fractional-N PLLs and Building Blocks

Chair: Joseph Cali, BAE Systems, USA — Co-Chair: Howard C. Luong, HKUST, China



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¹Zhejiang University, China  ; ²UESTC, China 
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Chair: Alyosha Molnar, Cornell University, USA — Co-Chair: François Rivet, University of Bordeaux, France

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¹GLOBALFOUNDRIES, India  ; ²IIT Guwahati, India 
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¹Oregon State University, USA  ; ²Columbia University, USA 




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Chair: Jane Gu, University of California, Davis, USA — Co-Chair: Arun Natarajan, Oregon State University, USA
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¹IBM T.J. Watson Research Center, USA **A** ; ²Fujikura, Japan **A**
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¹Samsung, USA **A** ; ²Samsung, Korea **A**
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Matan Gal-Katziri, Craig Ives, Armina Khakpour, Ali Hajimiri, Caltech, USA **A**





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Sébastien Sadlo¹, Magali De Matos², Andreia Cathelin¹, Nathalie Deltimple²
¹STMicroelectronics, France **A** ; ²IMS (UMR 5218), France **A**
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Ahmed S.H. Ahmed¹, Utku Soylu², Munkyo Seo³, Miguel Urteaga⁴, Mark J.W. Rodwell²
¹Marki Microwave, USA **A** ; ²University of California, Santa Barbara, USA **A** ;
³Sungkyunkwan University, Korea **A** ; ⁴Teledyne Scientific & Imaging, USA **A**
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Chair: Bahar Jalali Farahani, Acacia Communications, USA — Co-Chair: Alyssa Apse, Cornell University, USA
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Sandeep Hari, Cody J. Ellington, Brian A. Floyd, North Carolina State University, USA **A**

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Chair: Wanghua Wu, Samsung, USA — Co-Chair: Andreia Cathelin, STMicroelectronics, France
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Qiyao Jiang, Quan Pan, SUSTech, China **A**

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Chair: Alexandre Giry, CEA-Leti, France — Co-Chair: Xun Luo, UESTC, China












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¹Zhejiang University, China ; *²Integrated Beam Tech, China* ; *³University of California, Davis, USA* 
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¹Samsung, USA ; *²Samsung, Korea* 

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Chair: Ehsan Afshari, University of Michigan, USA — Co-Chair: Pietro Andreani, Lund University, Sweden

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¹Università di Padova, Italy ; *²Infineon Technologies, Austria* 
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Yiyang Shu¹, Huizhen Jenny Qian¹, Xiang Gao², Xun Luo¹
¹UESTC, China ; *²Zhejiang University, China* 
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Thomas Tapen¹, Andreia Cathelin², Alyssa Apsel¹
¹Cornell University, USA ; *²STMicroelectronics, France* 

RTu3G: RF Systems for Emerging Wireless Applications

Chair: Vadim Issakov, Technische Universität Braunschweig, Germany

Co-Chair: Mona M. Hella, Rensselaer Polytechnic Institute, USA










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¹STMicroelectronics, France  ; ²IEMN (UMR 8520), France  ; ³University of California, Berkeley, USA 
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Muhammad Ibrahim Wasiq Khan¹, Jongchan Woo¹, Xiang Yi¹, Mohamed I. Ibrahim¹, Rabia Tugce Yazicigil², Anantha Chandrakasan¹, Ruonan Han¹
¹MIT, USA  ; ²Boston University, USA 
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RTu4E: mm-Wave Circuits for Emerging Applications

Chair: Jeyanandh Paramesh, Carnegie Mellon University, USA — Co-Chair: Hongtao Xu, Fudan University, China

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







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¹EnSilica, UK  ; ²Satellite Applications Catapult, UK 
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Sumit Pratap Singh, Timo Rahkonen, Marko E. Leinonen, Aarno Pärssinen, University of Oulu, Finland 

RTu4G: Efficient Radios for IoT, GPS, WiFi, and Cellular

Chair: Roxann Broughton-Blanchard, Analog Devices, USA

Co-Chair: Arun Paidimarri, IBM T.J. Watson Research Center, USA

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Kejian Shi¹, Hooman Darabi², Asad A. Abidi¹
¹University of California, Los Angeles, USA  ; ²Broadcom, USA 
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Carl Bryant¹, Manel Collados¹, Ben Abdeljelil¹, Paul Fowers¹, Mohammed Hassan¹, David Ivory-Cave¹, Dimitris Nalbantis¹, Jon Strange¹, Levine Chen², Johoo Lin²
¹MediaTek, UK  ; ²MediaTek, Taiwan 
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Trevor J. Odelberg, Jaeho Im, David D. Wentzloff, University of Michigan, USA 
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¹University of Michigan, USA  ; ²University of Virginia, USA 
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